

REMARKS

The new claim 19 added above is copied from, and is intended to correspond exactly to, claim 6 of U.S. Pat. No. 6,115,399 issued September 5, 2000 to Shakuda. This claim is being copied into the present application to ensure compliance with 35 U.S.C. § 135(b). The Applicants suggest that an appropriate Count would read:

Count 2. A semiconductor light emitting device comprising:

a substrate; and

GaN-type compound semiconductor layers stacked on the substrate,

the GaN-type layers including

at least one active layer,

at least one n-type layer, and

at least one p-type layer;

wherein

a band gap energy of the one n-type layer

is smaller than

a band gap energy of the one p-type layer.

The Applicants further submit that claim 19 of the present application and at least claim 6 of U.S. Pat. No. 6,115,399 would correspond to the proposed Count. The Applicants also submit that they would expect the remaining claims of U.S. Pat. No. 6,115,399, *i.e.*, claims 1-5 and 7-23, would be designated as corresponding to this Count.

If any questions remain, the Examiner is respectfully invited to contact the undersigned.

Respectfully submitted,

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Attachment: Appendix page 5

APPENDIX
VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claim 19 is new.

END OF APPENDIX